# MSB92ASWT1G, MSB92AS1WT1G

# PNP Silicon General Purpose High Voltage Transistor

This PNP Silicon Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

#### Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	-300	Vdc
Collector-Emitter Voltage	V <sub>(BR)CEO</sub>	-300	Vdc
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ic	500	mAdc
ESD Rating: Human Body Model Machine Model	ESD	Class 1C Class C	-

#### THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P <sub>D</sub>	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

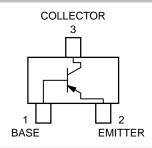
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



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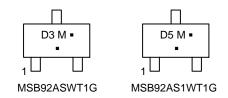
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SC-70 (SOT-323) CASE 419 STYLE 3

## **MARKING DIAGRAM**



Dx = Device Code
M = Date Code\*
• = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MSB92ASWT1G	SC-70 (Pb-Free)	3000/Tape & Reel
MSB92AS1WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	-300	-	Vdc
Collector-Base Breakdown Voltage $(I_C = -100 \mu Adc, I_E = 0)$	V <sub>(BR)</sub> CBO	-300	-	Vdc
Emitter-Base Breakdown Voltage $(I_E = -100 \mu Adc, I_E = 0)$	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = 300 Vdc, I <sub>E</sub> = 0)	Ісво	_	-0.25	μΑ
Emitter–Base Cutoff Current (V <sub>EB</sub> = -3.0 Vdc, I <sub>B</sub> = 0)	I <sub>EBO</sub>	_	-0.1	μΑ
DC Current Gain (Note 2)	h <sub>FE1</sub> h <sub>FE2</sub> h <sub>FE3</sub>	120 40 25	200 - -	_
Collector-Emitter Saturation Voltage (Note 2) $(I_C = -20 \text{ mAdc}, I_B = -2.0 \text{ mAdc})$	V <sub>CE(sat)</sub>	_	-0.5	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = –20 mAdc, I <sub>B</sub> = –2.0 mAdc)	V <sub>BE(sat)</sub>	_	-0.9	Vdc
SMALL SIGNAL CHARACTERISTICS	·			
Current Cain Bandwidth Braduct		50		MUZ

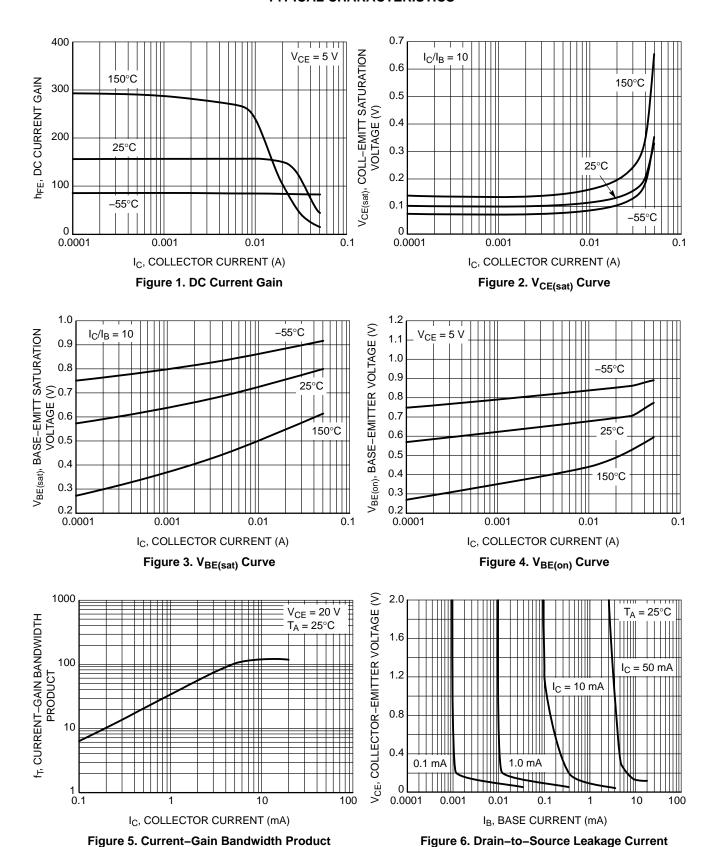
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mAdc, V <sub>CE</sub> = –20 Vdc, f = 20 MHz)	f <sub>T</sub>	50	-	MHz
Collector–Base Capacitance (V <sub>CB</sub> = -20 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	-	6.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width  $\leq$  300 µs, D.C.  $\leq$  2%.

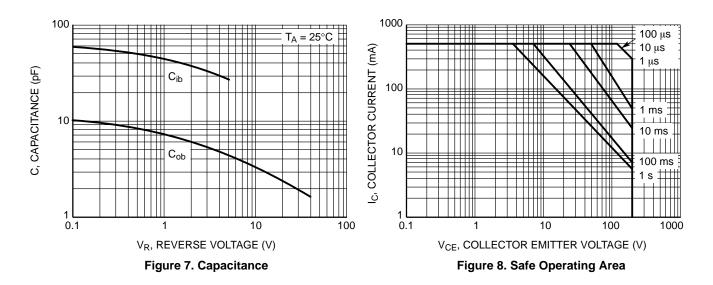
## MSB92ASWT1G, MSB92AS1WT1G

## **TYPICAL CHARACTERISTICS**



## MSB92ASWT1G, MSB92AS1WT1G

## **TYPICAL CHARACTERISTICS**







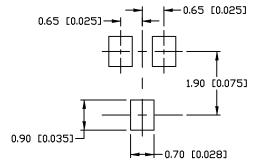
SC-70 (SOT-323) CASE 419 ISSUE P

**DATE 07 OCT 2021** 

#### NOTES:

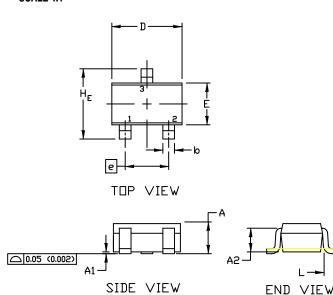
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Ε	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



# GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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